

Vishay Siliconix

Dual N-Channel 30-V (D-S) MOSFET

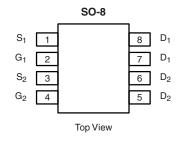
PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
30	0.035 at V _{GS} = 10 V	6.0		
	0.052 at V _{GS} = 4.5 V	4.9		

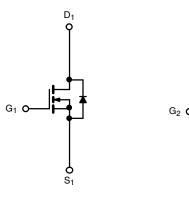
FEATURES

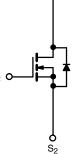
- Halogen-free According to IEC 61249-2-21
 Definition
- Compliant to RoHS Directive 2002/95/EC



FREE Available







 D_2

Ordering Information: Si9936BDY-T1-E3 (Lead (Pb)-free) Si9936BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	30		v	
Gate-Source Voltage		V _{GS}	± 20			
	T _A = 25 °C	- I _D	6.0	4.5		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		4.8	3.6		
Pulsed Drain Current		I _{DM}	40		A	
Continuous Source Current (Diode Conduction) ^a		۱ _S	1.7	0.9		
	T _A = 25 °C	- P _D	2.0	1.1	- w	
Maximum Power Dissipation ^a	T _A = 70 °C		1.3	0.7		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana haratian ta Antrianda	t ≤ 10 s	- R _{thJA}	53	62.5	°C/W
Maximum Junction-to-Ambient ^a	Steady State		92	110	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	30	40	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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SPECIFICATIONS $T_J = 25 \circ 0$	C, unless o	otherwise noted					
Parameter	Symbol	Test Conditions	Min. Ty		Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	1.0		3.0	V	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA	
Zava Cata Valtaga Dvain Cuvvant	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$	5		5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5$ V, $V_{GS} = 10$ V	40			А	
Drain-Source On-State Resistance ^a	D	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 6 \text{ A}$		0.028	0.035	0	
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 4.9 \text{ A}$	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 4.9 \text{ A}$		0.052	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 6 \text{ A}$		12		S	
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S}$ = 1.7 A, $V_{\rm GS}$ = 0 V		0.8	1.2	V	
Dynamic ^b			•				
Total Gate Charge	Qg			8.6	13		
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 6 \text{ A}$		1.8		nC	
Gate-Drain Charge	Q _{gd}			1.5		1	
Gate Resistance	Rg	f = 1 MHz		2.8		Ω	
Turn-On Delay Time	t _{d(on)}			10	15		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		15	25		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong\text{1}$ A, V_GEN = 10 V, R_g = 6 Ω		25	40	ns	
Fall Time	t _f			10	15		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 1.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		20	40		

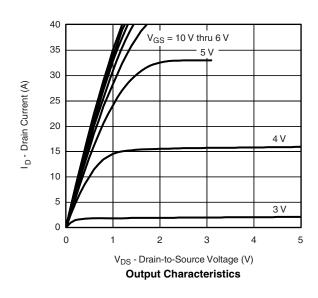
Notes:

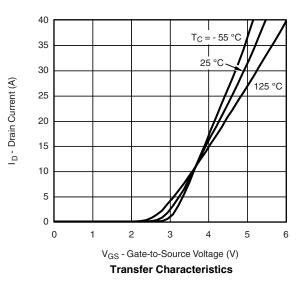
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

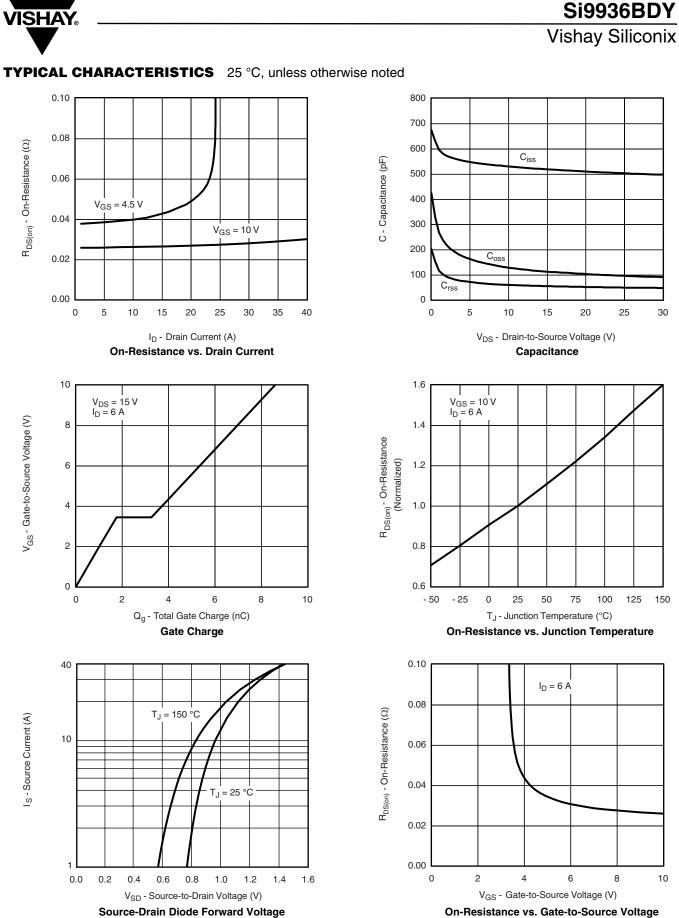
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







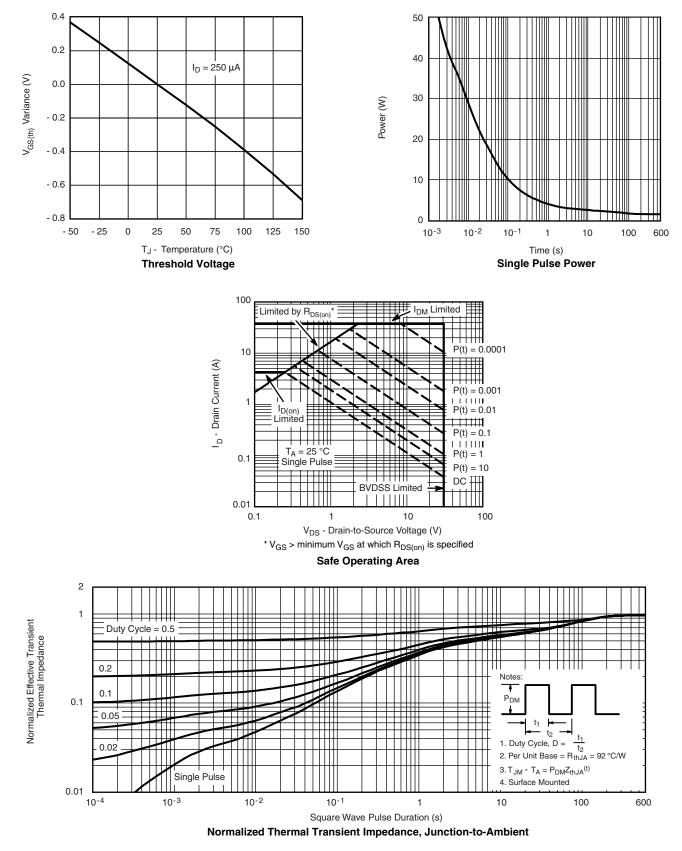
Source-Drain Diode Forward Voltage

Document Number: 72521 S09-0704-Rev. C, 27-Apr-09

Si9936BDY

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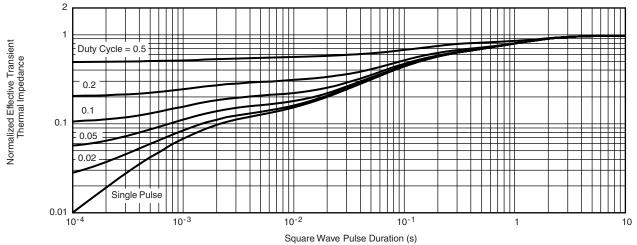




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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg772521.



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Revision: 01-Jan-2025

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